

# 2SK2315

# Silicon N Channel MOS FET

REJ03G1006-0200

(Previous: ADE-208-1354)

Rev.2.00 Sep.07,2005

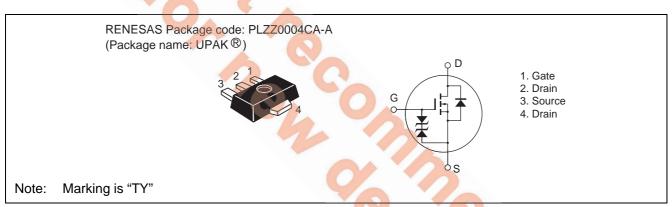
#### **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- 2.5 V gate drive device can be driven from 3 V source.
- Suitable for DC-DC converter, motor drive, power switch, solenoid drive

#### **Outline**



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# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	2	А
Drain peak current	I <sub>D(pulse)</sub> *1	4	А
Body to drain diode reverse drain current	I <sub>DR</sub>	2	А
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

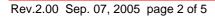
Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1 %

2. When using the alumina ceramic board (12.5  $\times$  20  $\times$  0.7mm)

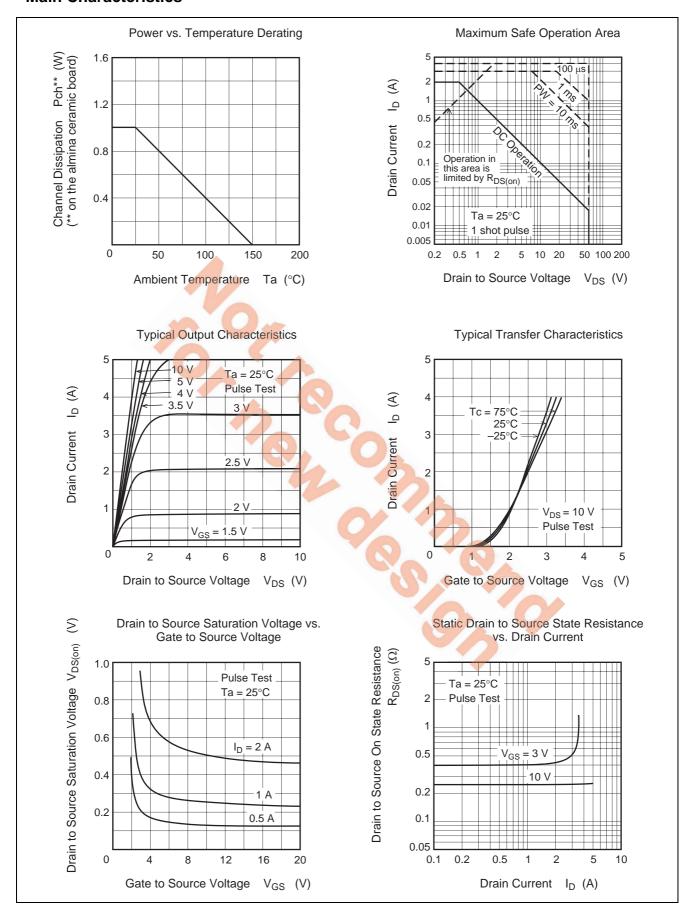
#### **Electrical Characteristics**

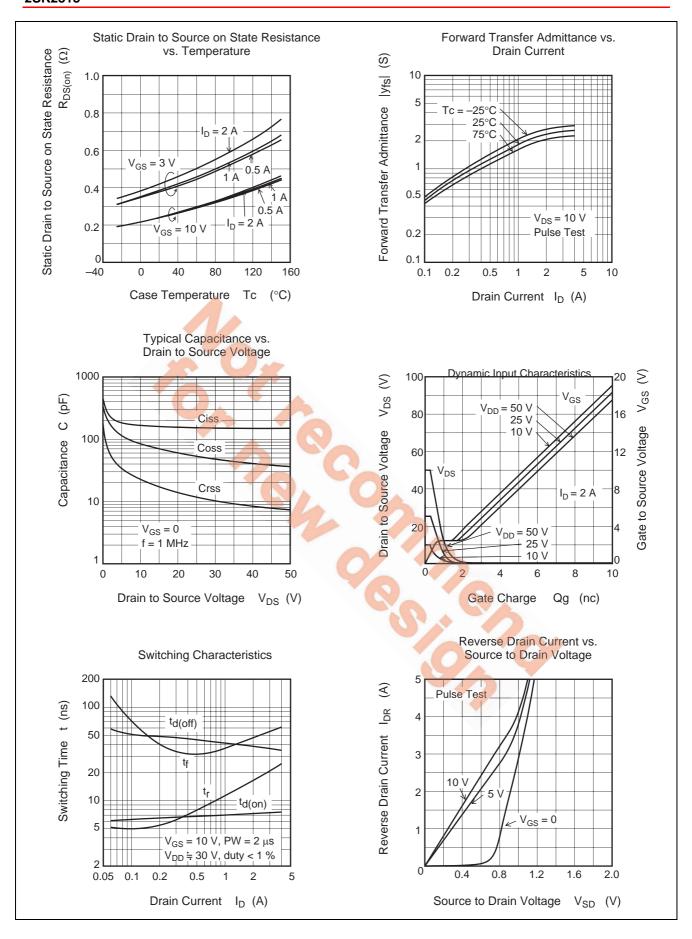
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	<b>6</b> 0	-	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	-	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	GSS	1	-	±5	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I <sub>DSS</sub>	-	_	5	μΑ	$V_{DS} = 50 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	0.5		1.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static drain to source on state	R <sub>DS(on)</sub>		0.4	0.6	Ω	$I_D = 0.3 \text{ A}, V_{GS} = 3 \text{ V}^{*3}$	
resistance		_	0.35	0.45	Ω	$I_D = 1 A, V_{GS} = 4 V^{*3}$	
Forward transfer admittance	y <sub>fs</sub>	1.5	1.8	_	S	$I_D = 1 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$	
Input capacitance	Ciss		173	<u> </u>	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	1	85		pF	f = 1 MHz	
Reverse transfer capacitance	Crss		23	F-A	pF		
Turn-on time	ton		21	<b>-</b>	ns	$I_D = 1 \text{ A}, R_L = 30 \Omega,$	
Turn-off time	t <sub>off</sub>		85		ns	V <sub>GS</sub> = 10 V	
Note: 3. Pulse Test							

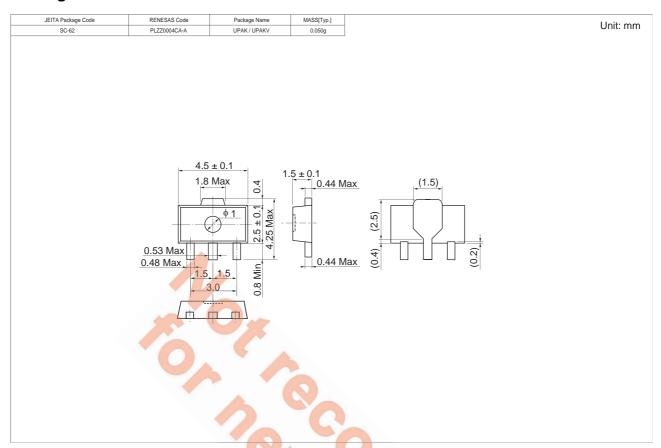


#### **Main Characteristics**





### **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
2SK2315TYTL-E	1000 pcs	Taping
2SK2315TYTR-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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